

WHAT IS CLAIMED IS:

Sub A47

1 A wavelength monitoring apparatus comprising:
an optical device made of a periodic multilayer structure;
a beam source optically coupled to at least one end surface
5 of said periodic multilayer structure, said one end surface being
not parallel to layer surfaces of said periodic multilayer
structure; and

beam detecting means for detecting beam made to exit from
at least one surface of said periodic multilayer structure at
10 a specific angle with respect to a specific wavelength, said
one surface being parallel to said layer surfaces of said periodic
multilayer structure.

2. A wavelength monitoring apparatus according to claim
1, wherein said optical device is made of a multilayer film formed
15 on a substrate transparent to the wavelength used.

3. A wavelength monitoring apparatus according to claim
1, wherein said optical device is made of the periodic multilayer
structure having layer surfaces perpendicular to a surface of
a substrate.

20 4. A wavelength monitoring apparatus according to claim
1, wherein said beam source is constituted by a semiconductor
laser.

5. A wavelength monitoring apparatus according to claim
1, wherein said beam detecting means is constituted by at least
25 one photo detector.

6. A wavelength monitoring apparatus according to claim 2, wherein said optical device, a semiconductor laser and a photo detector are mounted on one and the same substrate.

5 7. A wavelength monitoring apparatus according to claim 6, wherein beam emitted from said semiconductor laser is coupled to a beam incidence end surface of said multilayer film by level differences provided on said substrate on which said multilayer film is formed.

10 8. A wavelength monitoring apparatus according to claim 6, wherein said photo detector is provided on a surface opposite to said surface of said substrate on which said multilayer film is formed.

15 9. A wavelength monitoring apparatus according to claim 3, wherein said optical device, a semiconductor laser and a photo detector are mounted on one and the same substrate.

20 10. A wavelength monitoring apparatus comprising:
an optical device having a periodic multilayer structure, said periodic multilayer structure defining, at least, a first surface substantially perpendicular to layer surfaces of the periodic multilayer structure and a second surface substantially parallel to the layer surfaces of the periodic multilayer structure;

25 a semiconductor laser confronted with said first surface;
and
a photo detector confronted with said second surface.

11. A wave length monitoring apparatus according to claim 10, further comprising:

a common substrate supporting said optical device, said semiconductor laser and said photo detector.

5 12. A wave length monitoring apparatus according to claim 11, wherein said substrate is transparent, and is contacted with the second surface of said periodic multilayer structure.

10 13. A wave length monitoring apparatus according to claim 11, wherein said substrate is contacted with a surface of said periodic multilayer structure other than said first and second surfaces.

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